TRENCH STRUCTURE IN MULTILAYER WAFER

Abstract

The present invention relates to a method for the manufacture of a trench structure in a multilayer wafer comprising a substrate, an oxide layer on the substrate and a semiconductor layer on the oxide layer, the method comprising the steps of forming a trench through the semiconductor layer and the oxide layer and extending into the substrate and performing an anneal treatment of the formed trench such that at the inner surface of the trench some material of the semiconductor layer flows at least over a portion of the part of the oxide layer exposed at the inner surface of the trench.

Fig. 2